TS5USBC400 Dual 2:1 USB 2.0 Mux/DeMux with 16-V Overvoltage Protection

1 Features

- Supply Range 2.3 V to 5.5 V
- Differential 2:1 or 1:2 Switch/Multiplexer
- 0-V to 16-V Overvoltage Protection (OVP) on Common Pins
- Powered Off Protection When V_{CC} = 0 V
- Low R_{ON} of 9 Ω Maximum
- BW of 1.1 GHz Typical
- C_{ON} of 4.5 pF Typical
- Low Power Disable Mode
- 1.8-V Compatible Logic Inputs
- ESD Protection Exceeds JESD 22
  - 2000-V Human Body Model (HBM)
- TS5USBC400: Standard Temperature Range of 0°C to 70°C
- TS5USBC400I: Industrial Temperature Range of -40°C to 85°C
- Small DSBGA Package

2 Applications

- Mobile
- PC/Notebook
- Tablet
- Anywhere a USB Type-C™ or Micro-B Connector is Used

3 Description

The TS5USBC400 is a bidirectional low-power dual port, high-speed, USB 2.0 analog switch with integrated protection for USB Type-C™ systems. The device is configured as a dual 2:1 or 1:2 switch and is optimized for handling the USB 2.0 D+/- lines in a USB Type-C™ systems.

The TS5USBC400 protection on the I/O pins can tolerate up to 16V with automatic shutoff circuitry to protect system components behind the switch.

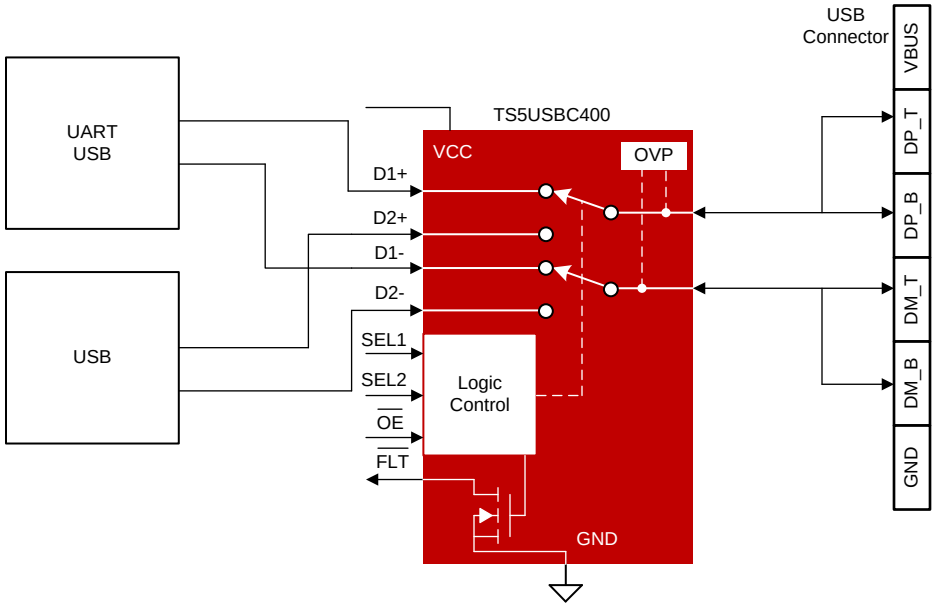
The TS5USBC400 comes in a small 12 pin DSBGA package making it a perfect candidate for mobile and space constrained applications.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TS5USBC400 TS5USBC400I	DSBGA (12)	1.582 mm × 1.182 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Schematic



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4 Revision History

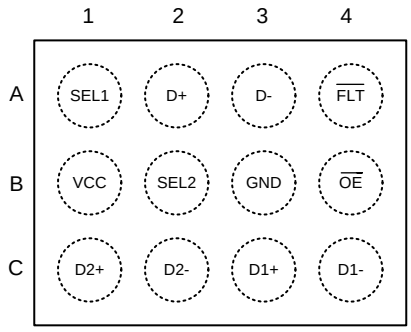
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Original (September 2017) to Revision A	Page
• Added I_{CC} Active supply current and Supply current during OVP condition to the E*lectrical Specification* table	4

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5 Pin Configuration and Functions

YFP Package
12-Pin DSBGA
Top View



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
SEL1	A1	I	Switch select1 (Active high)
D+	A2	I/O	Data switch input (Differential +)
D–	A3	I/O	Data switch input (Differential –)
$\overline{FLT}$	A4	O	Fault indicator output pin (Active low) - open drain
VCC	B1	PWR	Supply Voltage
SEL2	B2	I	Switch select2 (Active high)
GND	B3	GND	Ground
$\overline{OE}$	B4	I	Output enable (Active low)
D2+	C1	I/O	Data switch output 2 (Differential +)
D2–	C2	I/O	Data switch output 2 (Differential -)
D1+	C3	I/O	Data switch output 1 (Differential +)
D1–	C4	I/O	Data switch output 1 (Differential -)

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6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1) (2)

			MIN	MAX	UNIT
V_{CC}	Supply voltage(3)		–0.5	6	V
$V_{I/O}$	Input/Output DC voltage (D+, D-)(3)		–0.5	18	V
$V_{I/O}$	Input/Output DC voltage (D1+/D1-, D2+/D2-) (3)		–0.5	6	V
V_I	Digital input voltage (SEL1, SEL2, $\overline{OE}$)		–0.5	6	V
V_O	Digital output voltage ($\overline{FLT}$)		–0.5	6	V
I_K	Input-output port diode current (D+, D-, D1+, D1-, D2+, D2-)	$V_{IN} < 0$	–50		mA
I_{IK}	Digital logic input clamp current (SEL1, SEL2, $\overline{OE}$) (3)	$V_I < 0$	–50		mA
I_{CC}	Continuous current through VCC			100	mA
I_{GND}	Continuous current through GND		–100		mA
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
(3) All voltages are with respect to ground, unless otherwise specified.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

		MIN	MAX	UNIT
V_{CC}	Supply voltage	2.3	5.5	V
$V_{I/O\ (D+,\ D-)}$	Analog input/output voltage	0	18	V
$V_{I/O\ (D1,\ D1-,\ D2+,\ D2-)}$		0	3.6	V
V_I	Digital input voltage (SEL1, SEL2, $\overline{OE}$)	0	5.5	V
V_O	Digital output voltage ($\overline{FLT}$)	0	5.5	V
$I_{I/O\ (D+,\ D-,\ D1+,\ D1-,\ D2+,\ D2-)}$	Analog input/output port continuous current	-50	50	mA
I_{OL}	Digital output current		3	mA
T_A	Operating free-air temperature (TS5USBC400) Standard	0	70	ºC
T_A	Operating free-air temperature (TS5USBC400I) Industrial	–40	85	ºC
T_J	Junction temperature	–40	125	ºC

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6.4 Thermal Information

THERMAL METRIC (1)		TS5USBC400 YFP 12 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	91.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	0.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	22.8	°C/W
ψ_{JT}	Junction-to-top characterization parameter	0.5	°C/W
ψ_{JB}	Junction-to-board characterization parameter	23.0	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

T_A = –40°C to +85°C (Industrial), TA = 0°C to 70°C (Standard), V_{CC} = 2.3 V to 5.5 V, GND = 0V, Typical values are at V_{CC} = 3.3 V, T_A = 25°C, (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY						
V_{CC}	Power supply voltage		2.3		5.5	V
I_{CC}	Active supply current	$\overline{OE}$ = 0 V SEL1, SEL2 = 0 V, 1.8 V or V_{CC} 0 V < $V_{I/O}$ < 3.6 V		72	100	µA
	Supply current during OVP condition	$\overline{OE}$ = 0 V SEL1, SEL2 = 0 V, 1.8 V or V_{CC} $V_{I/O}$ > V_{POS_THLD}		80	120	µA
I_{CC_PD}	Standby powered down supply current	$\overline{OE}$ = 1.8 V or V_{CC} SEL1 = 0 V, 1.8 V, or VCC SEL2 = 0 V, 1.8 V, or VCC		2.2	10	µA
DC Characteristics						
R_{ON}	ON-state resistance	$V_{I/O}$ = 0.4 V I_{SINK} = 8 mA Refer to ON-State Resistance Figure		5.6	9	Ω
ΔR_{ON}	ON-state resistance match between channels	$V_{I/O}$ = 0.4 V I_{SINK} = 8 mA Refer to ON-State Resistance Figure		0.07	0.3	Ω
$R_{ON\ (FLAT)}$	ON-state resistance flatness	$V_{I/O}$ = 0 V to 0.4 V I_{SINK} = 8 mA Refer to ON-State Resistance Figure		0.07	0.4	Ω
I_{OFF}	I/O pin OFF leakage current	$V_{D\pm}$ = 0 V or 3.6 V V_{CC} = 2.3 V to 5.5 V $V_{D1\pm}$or $V_{D2+/-}$ = 3.6 V or 0 V Refer to Off Leakage Figure	-1	1.2	6	µA
		$V_{D\pm}$ = 0 V or 16 V V_{CC} = 2.3 V to 5.5 V $V_{D1\pm}$ or $V_{D2+/-}$ = 0 V Refer to Off Leakage Figure	-1	165	200	µA
I_{ON}	ON leakage current	$V_{D\pm}$ = 0 V or 3.6 V $V_{D1\pm}$ and $V_{D2+/-}$ = high-Z Refer to On Leakage Figure	-1	1.2	6	µA
Digital Characteristics						
V_{IH}	Input logic high	SEL1, SEL2, $\overline{OE}$	1.4			V
V_{IL}	Input logic low	SEL1, SEL2, $\overline{OE}$			0.5	V
V_{OL}	Output logic low	$\overline{FLT}$ I_{OL} = 3 mA			0.4	V
I_{IH}	Input high leakage current	SEL1, SEL2, $\overline{OE}$ = 1.8 V, V_{CC}	-1	1	5	µA
I_{IL}	Input low leakage current	SEL1, SEL2, $\overline{OE}$ = 0 V	-1	±0.2	5	µA

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Electrical Characteristics (continued)

T_A = –40°C to +85°C (Industrial), TA = 0°C to 70°C (Standard), V_{CC} = 2.3 V to 5.5 V, GND = 0V, Typical values are at V_{CC} = 3.3 V, T_A = 25°C, (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
R_{PD}	Internal pull-down resistor on digital input pins			6		MΩ
C_I	Digital input capacitance	SEL1, SEL2 = 0 V, 1.8 V or VCC f = 1 MHz		3.4		pF
Protection						
V_{OVP_TH}	OVP positive threshold		4.5	4.8	5.2	V
V_{OVP_HYST}	OVP threshold hysteresis		75	230	425	mV
V_{CLAMP_V}	Maximum voltage to appear on D1± and D2± pins during OVP scenario	$V_{D±}$ = 0 to 18 V t_{RISE} and t_{FALL}(10% to 90 %) = 100 ns R_L = Open Switch on or off $\overline{OE}$ = 0 V	0		9.6	V
		$V_{D±}$ = 0 to 18 V t_{RISE} and t_{FALL}(10% to 90 %) = 100 ns R_L = 50Ω Switch on or off $\overline{OE}$ = 0 V	0		9.0	V
t_{EN_OVP}	OVP enable time	R_{PU} = 10 kΩ to VCC ($\overline{FLT}$) C_L = 35 pF Refer to OVP Timing Diagram Figure		0.6	3	µs
t_{REC_OVP}	OVP recovery time	R_{PU} = 10 kΩ to VCC ($\overline{FLT}$) C_L = 35 pF Refer to OVP Timing Diagram Figure		1.5	5	µs

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6.6 Dynamic Characteristics

T_A = –40°C to +85°C (Industrial), TA = 0°C to 70°C (Standard), V_{CC} = 2.3 V to 5.5V, GND = 0V, Typical values are at V_{CC} = 3.3 V, T_A = 25°C, (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
C_{OFF}	D+, D- off capacitance	$\overline{V_{D+/-}}$ = 0 or 3.3 V, $\overline{OE}$ = V_{CC} f = 240 MHz	Switch OFF	1.2	3.5	6.2	pF
	D1+, D1-, D2+, D2- off capacitance	$\overline{V_{D+/-}}$ = 0 or 3.3 V, $\overline{OE}$ = V_{CC} or $\overline{OE}$ = 0V with SEL1, SEL2 (switch not selected) f = 240 MHz	Switch OFF or not selected	1.2	3.5	6.2	pF
C_{ON}	IO pins ON capacitance	$V_{D+/-}$ = 0 or 3.3 V, f = 240 MHz	Switch ON	1.4	4.5	6.2	pF
O_{ISO}	Differential off isolation	RL = 50 Ω CL = 5 pF f = 100 kHz Refer to Off Isolation Figure	Switch OFF		-90		dB
		RL = 50 Ω CL = 5 pF f = 240 MHz Refer to Off Isolation Figure	Switch OFF		-22		dB
X_{TALK}	Channel to Channel crosstalk	RL = 50 Ω CL = 5 pF f = 100 kHz Refer to Crosstalk Figure	Switch ON		-90		dB
BW	Bandwidth	RL = 50 Ω; Refer to BW and Insertion Loss Figure	Switch ON		1.1		GHz
I_{LOSS}	Insertion loss	RL = 50 Ω f = 240 MHz; Refer to BW and Insertion Loss Figure	Switch ON		-0.7		dB

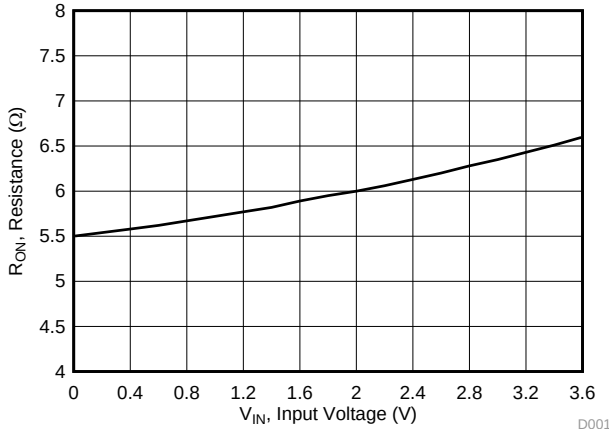
6.7 Timing Requirements

T_A = –40°C to +85°C (Industrial), TA = 0°C to 70°C (Standard), V_{CC} = 2.3 V to 5.5V, GND = 0V, Typical values are at V_{CC} = 3.3 V, T_A = 25°C, (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	NOM	MAX	UNIT
t_{switch}	Switching time between channels (SEL1, SEL2 to output)	$V_{D+/-}$ = 0.8 V Refer to Tswitch Timing Figure	R_L = 50 Ω, C_L = 5 pF, V_{CC} = 2.3 V to 5.5 V		0.45	1.2	µs
t_{on}	Device turn on time ($\overline{OE}$ to output)	$V_{D+/-}$ = 0.8 V Refer to Ton and Toff Figure			100	250	µs
t_{off}	Device turn off time ($\overline{OE}$ to output)	$V_{D+/-}$ = 0.8 V Refer to Ton and Toff Figure			0.35	1	µs
$t_{SK(P)}$	Skew of opposite transitions of same output (between D+ and D-)	$V_{D+/-}$ = 0.4 V Refer to Tsk Figure	R_L = 50 Ω, C_L = 1 pF, V_{CC} = 2.3 V to 5.5 V		9	50	ps
t_{pd}	Propagation delay	$V_{D+/-}$ = 0.4 V Refer to Tpd Figure	R_L = 50 Ω, C_L = 5 pF, V_{CC} = 2.3 V to 5.5 V		130	180	ps

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6.8 Typical Characteristics

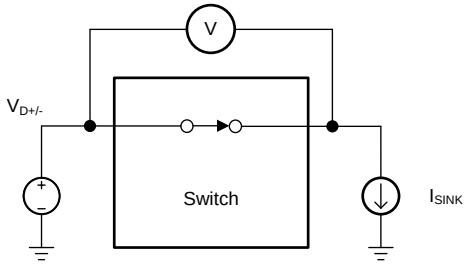


V_{CC} = 3.3 V T_A = 25°C

Figure 1. ON-Resistance vs Input Voltage

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7 Parameter Measurement Information



Channel ON, $R_{ON} = V/I_{SINK}$

Figure 2. ON-State Resistance (R_{ON})

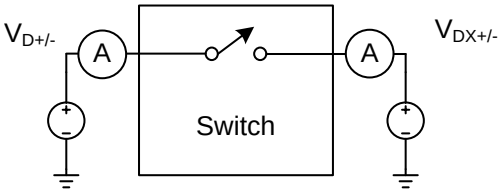


Figure 3. Off Leakage

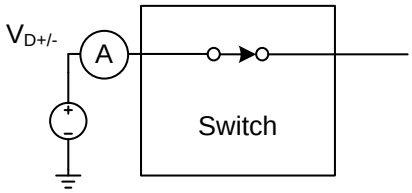
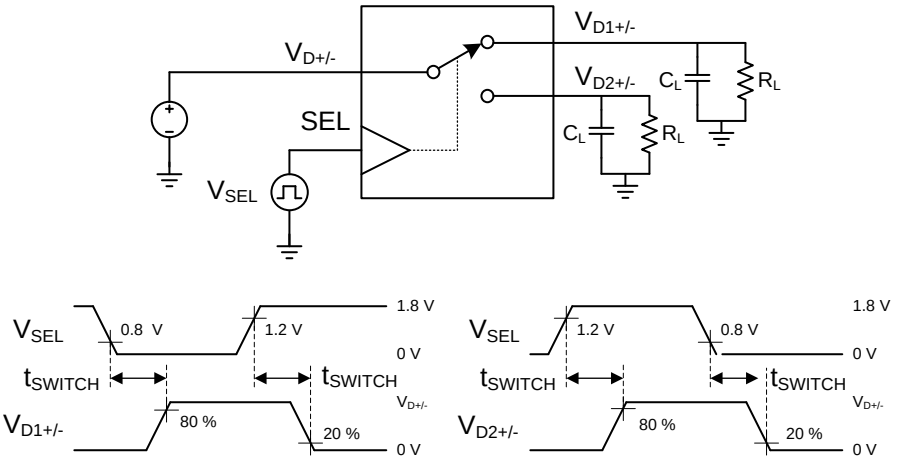


Figure 4. On Leakage



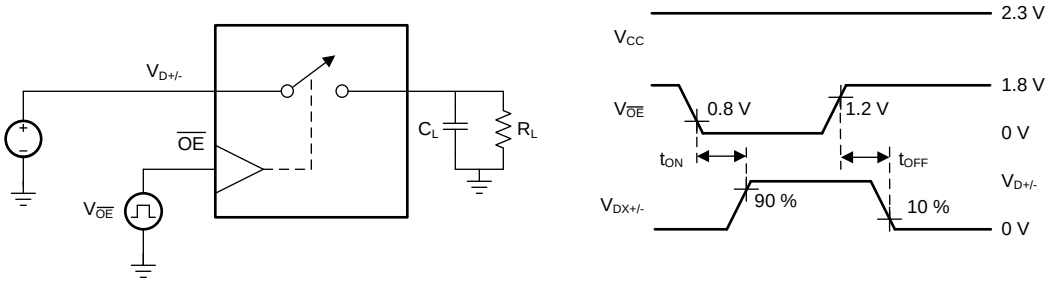
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(1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 500 ps, t_f < 500 ps.

(2) C_L includes probe and jig capacitance.

Figure 5. t_{SWITCH} Timing

Parameter Measurement Information (continued)

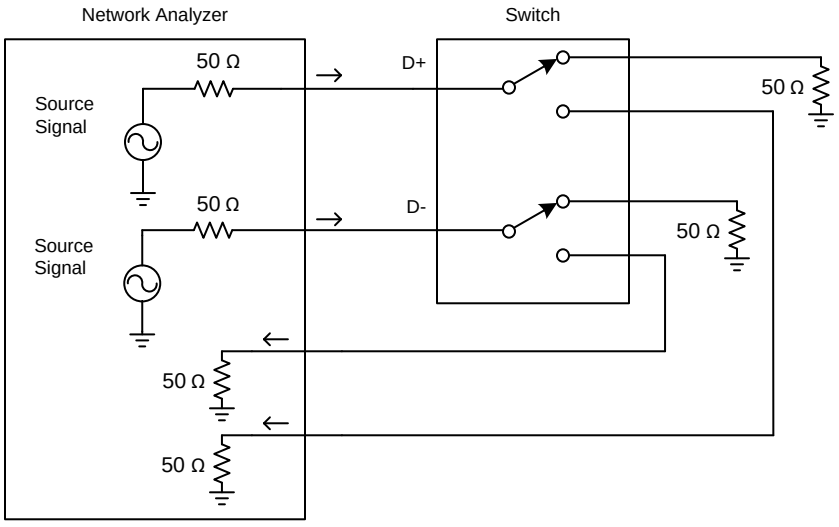


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(1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 500 ps, t_f < 500 ps.

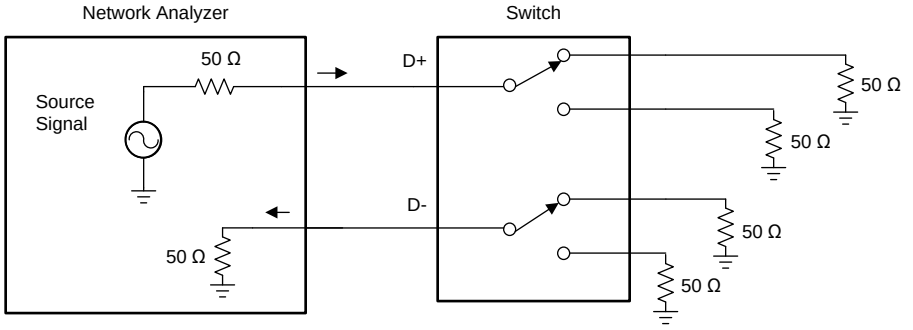
(2) C_L includes probe and jig capacitance.

Figure 6. t_{ON}, t_{OFF} for $\overline{OE}$



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Figure 7. Off Isolation

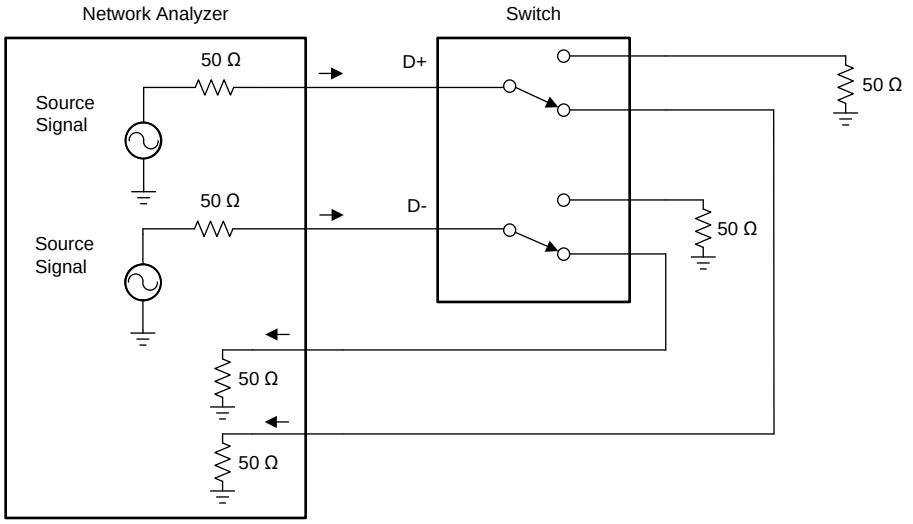


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Figure 8. Cross Talk

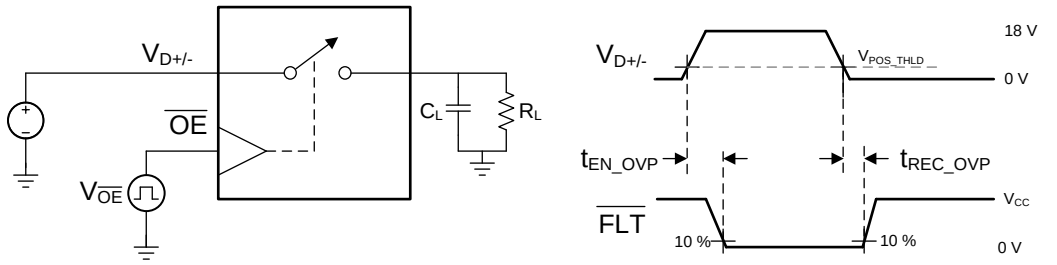
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Parameter Measurement Information (continued)



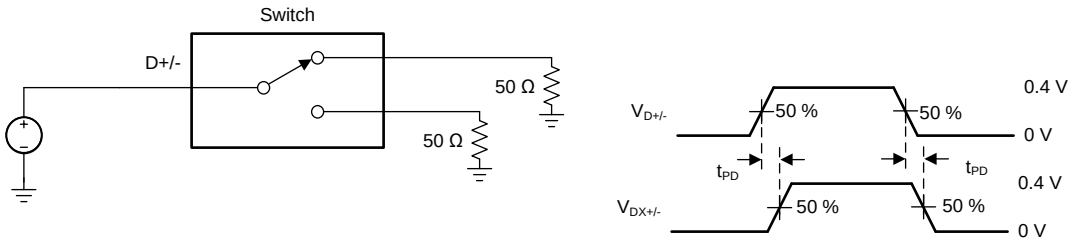
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Figure 9. BW and Insertion Loss



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Figure 10. t_{EN_OVP} and t_{DIS_OVP} Timing Diagram



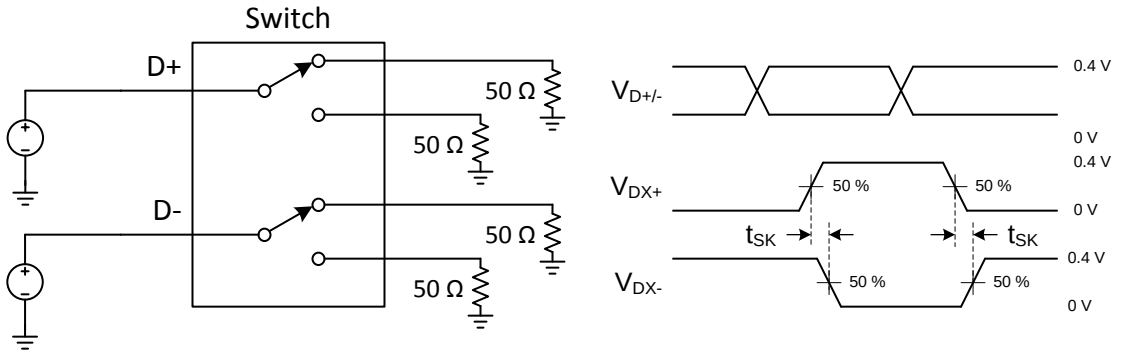
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(1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 500 ps, t_f < 500 ps.

(2) C_L includes probe and jig capacitance.

Figure 11. t_{PD}

Parameter Measurement Information (continued)



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(1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 500 ps, t_f < 500 ps.

(2) C_L includes probe and jig capacitance.

Figure 12. t_{SK}

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8 Detailed Description

8.1 Overview

The TS5USBC400 is a bidirectional low-power dual port, high-speed, USB 2.0 analog switch with integrated protection for USB Type-C systems. The device is configured as a dual 2:1 or 1:2 switch and is optimized for handling the USB 2.0 D+/- lines in a USB Type-C system as shown in Figure 13.

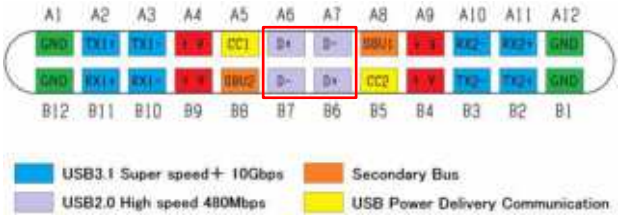
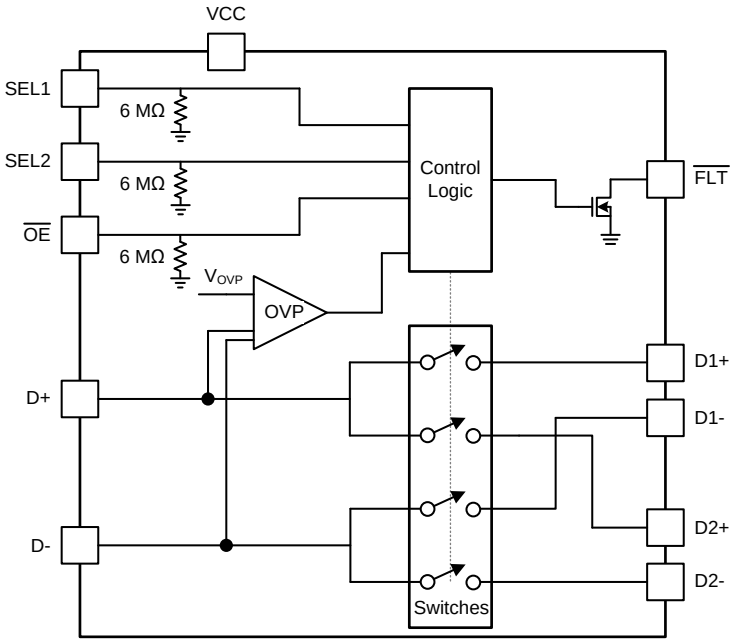


Figure 13. USB Type-C Connector Pinout

The TS5USBC400 also works in traditional USB systems that need protection from fault conditions such as automotive and applications that require higher voltage charging. The device maintains excellent signal integrity through the optimization of both R_{ON} and BW while protecting the system with 0 V to 16 V OVP protection. The OVP implementation is designed to protect sensitive system components behind the switch that cannot survive a fault condition where VBUS is shorted the D+ and D- pins on the connector.

8.2 Functional Block Diagram



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8.3 Feature Description

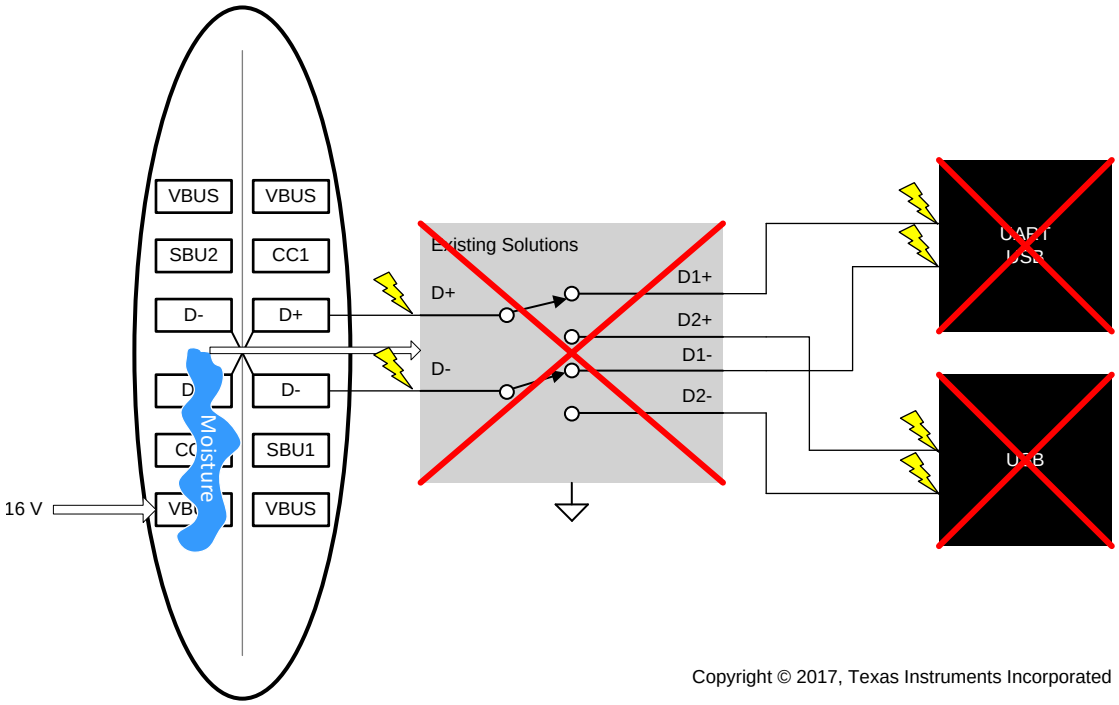
8.3.1 Powered-off Protection

When the TS5USBC400 is powered off the I/Os of the device remain in a high-Z state. The crosstalk, off-isolation, and leakage remain within the *Electrical Specifications*.

This prevents errant voltages from reaching the rest of the system and maintains isolation when the system is powering up.

8.3.2 Overvoltage Protection

The OVP of the TS5USBC400 is designed to protect the system from D+/- shorts to VBUS at the USB and USB Type-C connector. Figure 14 depicts a moisture short that would cause 16 V to appear on an existing USB solution that could pass through the device and damage components behind the device.



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Figure 14. Existing Solution Being Damaged by a Short, 16 V

The TS5USBC400 will open the switches and protect the rest of the system by blocking the 16 V as depicted in .

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Feature Description (continued)

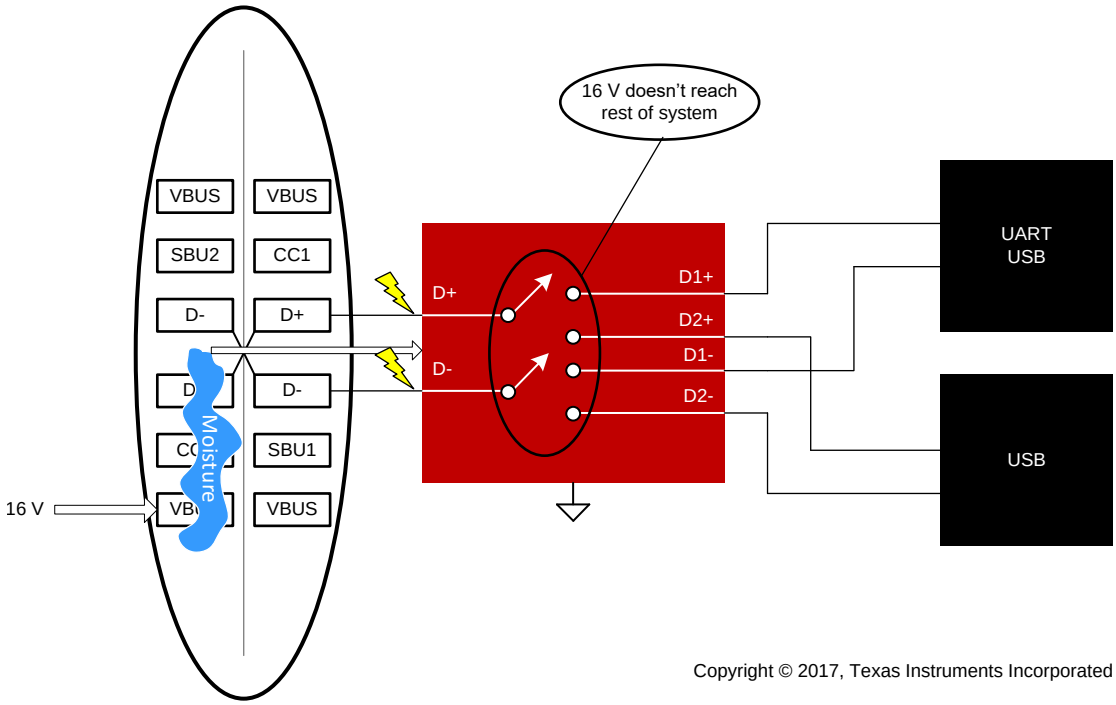


Figure 15. Protecting During a 16-V Short

Figure 16 is a waveform showing the voltage on the pins during an over-voltage scenario.

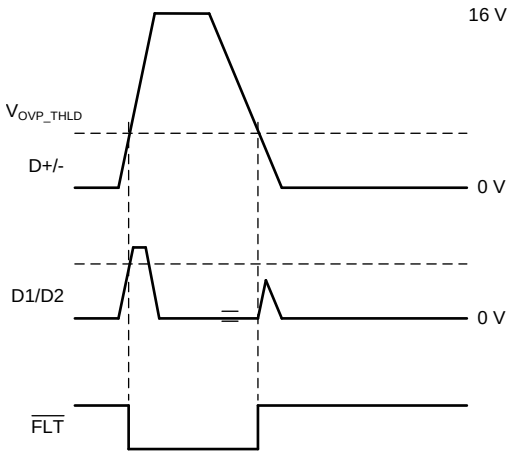


Figure 16. Overvoltage Protection Waveform, 16 V

8.4 Device Functional Modes

8.4.1 Pin Functions

Table 1. Function Table

$\overline{OE}$	SEL1	SEL2	D- Connection	D+ Connection
H	X	X	High-Z	High-Z
L	L	L	D- to D1-	D+ to D1+
L	L	H	D- to D1-	D+ to D2+
L	H	L	D- to D2-	D+ to D1+
L	H	H	D- to D2-	D+ to D2+

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9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

There are many USB applications in which the USB hubs or controllers have a limited number of USB I/Os or need to route signals from a single USB connector. The TS5USBC400 solution can effectively expand the limited USB I/Os by switching between multiple USB buses to interface them to a single USB hub or controller or route signals from on connector to two different locations. With independent control of the two switches using SEL1 and SEL2, TS5USBC400 can be used to cross switch single ended signals.

9.2 Typical Application

TS5USBC400 USB/UART switch. The TS5USBC400 is used to switch signals between the USB path, which goes to the baseband or application processor, or the UART path, which goes to debug port. The TS5USBC400 has internal 6-MΩ pull-down resistors on SEL1, SEL2, and $\overline{OE}$. The pull-down on SEL1 and SEL2 pins ensure the D1+/D1- channel is selected by default. The pull-down on $\overline{OE}$ enables the switch when power is applied.

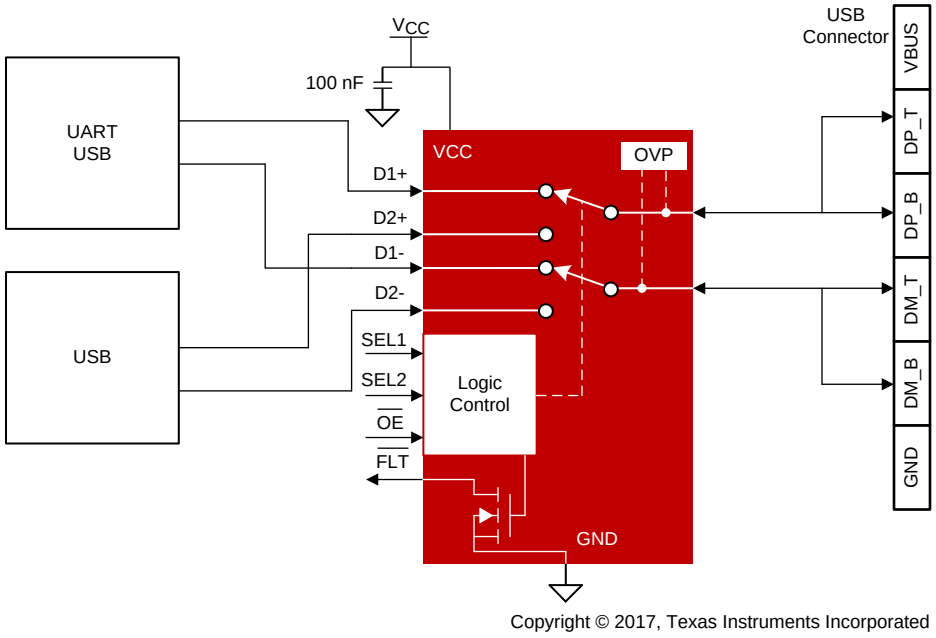


Figure 17. Typical TS5USBC400 Application

9.2.1 Design Requirements

Design requirements of USB 1.0,1.1, and 2.0 standards must be followed. The TS5USBC400 has internal 6-MΩ pulldown resistors on SEL1, SEL2, and $\overline{OE}$, so no external resistors are required on the logic pins. The internal pull-down resistor on SEL1 and SEL2 pins ensures the D1+ and D1- channels are selected by default. The internal pull-down resistor on $\overline{OE}$ enables the switch when power is applied to VCC.

9.2.2 Detailed Design Procedure

The TS5USBC400can be properly operated without any external components. However, TI recommends that unused pins must be connected to ground through a 50-Ω resistor to prevent signal reflections back into the device. TI does recommend a 100nF bypass capacitor placed close to TS5USBC400 VCC pin.

Typical Application (continued)

9.2.3 Application Curves

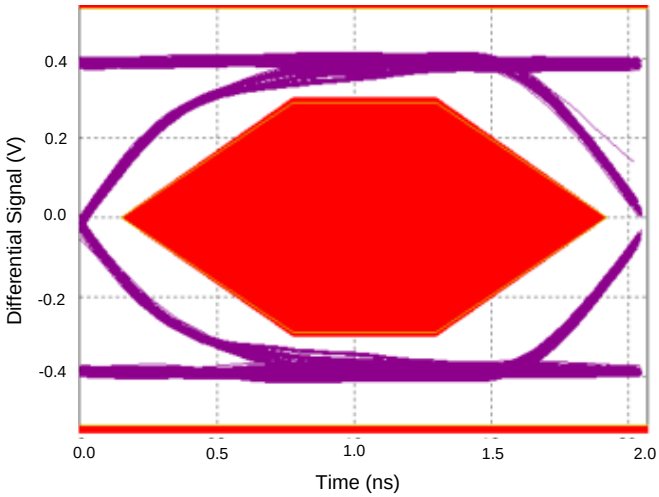


Figure 18. High Speed Eye Diagram With TS5USBC400

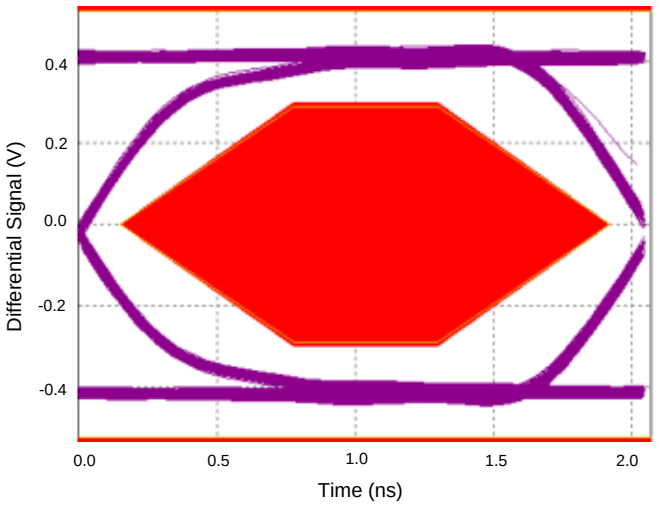


Figure 19. High Speed Eye Diagram Without TS5USBC400

10 Power Supply Recommendations

Power to the device is supplied through the VCC pin and must follow the USB 1.0, 1.1, and 2.0 standards. TI recommends placing a 100nF bypass capacitor as close to the supply pin VCC as possible to help smooth out lower frequency noise to provide better load regulation across the frequency spectrum.

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11 Layout

11.1 Layout Guidelines

1. Place supply bypass capacitors as close to VCC pin as possible and avoid placing the bypass caps near the D± traces.
2. The high-speed D± must match and be no more than 4 inches long; otherwise, the eye diagram performance may be degraded. A high-speed USB connection is made through a shielded, twisted pair cable with a differential characteristic impedance. In layout, the impedance of D+ and D– traces must match the cable characteristic differential impedance for optimal performance.
3. Route the high-speed USB signals using a minimum of vias and corners which reduces signal reflections and impedance changes. When a via must be used, increase the clearance size around it to minimize its capacitance. Each via introduces discontinuities in the signal's transmission line and increases the chance of picking up interference from the other layers of the board. Be careful when designing test points on twisted pair lines; through-hole pins are not recommended.
4. When it becomes necessary to turn 90°, use two 45° turns or an arc instead of making a single 90° turn. This reduces reflections on the signal traces by minimizing impedance discontinuities.
5. Do not route USB traces under or near crystals, oscillators, clock signal generators, switching regulators, mounting holes, magnetic devices or ICs that use or duplicate clock signals.
6. Avoid stubs on the high-speed USB signals because they cause signal reflections. If a stub is unavoidable, then the stub must be less than 200 mm.
7. Route all high-speed USB signal traces over continuous GND planes, with no interruptions.
8. Avoid crossing over anti-etch, commonly found with plane splits.
9. Due to high frequencies associated with the USB, a printed circuit board with at least four layers is recommended; two signal layers separated by a ground and power layer as shown in Figure 20.

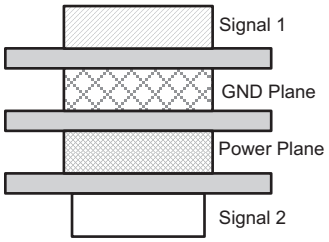


Figure 20. Four-Layer Board Stack-Up

The majority of signal traces must run on a single layer, preferably Signal 1. Immediately next to this layer must be the GND plane, which is solid with no cuts. Avoid running signal traces across a split in the ground or power plane. When running across split planes is unavoidable, sufficient decoupling must be used. Minimizing the number of signal vias reduces EMI by reducing inductance at high frequencies.

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11.2 Layout Example

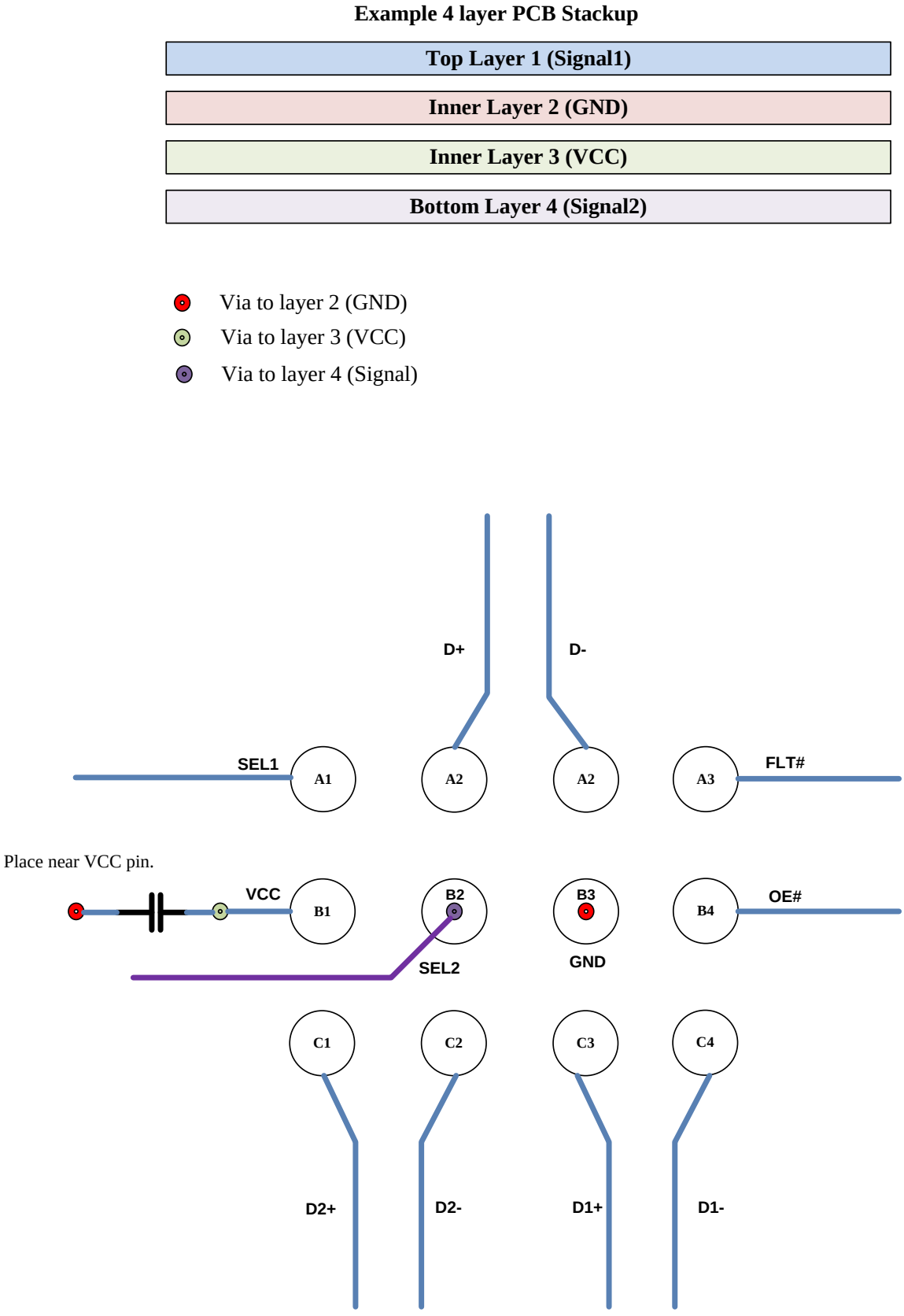


Figure 21. Layout Example

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12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- *USB 2.0 Board Design and Layout Guidelines*
- *High-Speed Layout Guidelines Application Report*
- *High-Speed Interface Layout Guidelines*

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

E2E is a trademark of Texas Instruments.
USB Type-C is a trademark of USB Implementers Forum.
All other trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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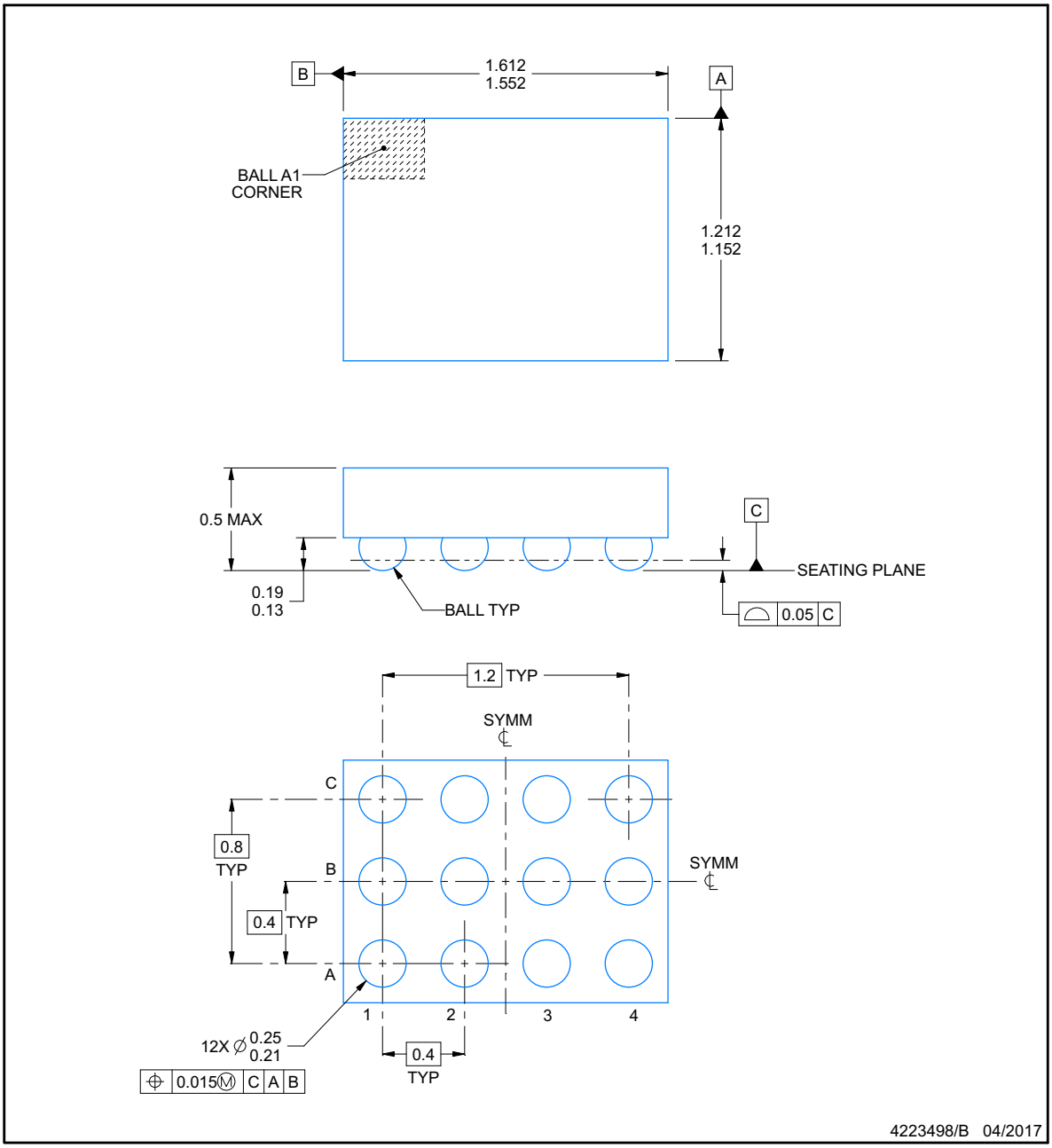
PACKAGE OUTLINE

YFP0012-C01



DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

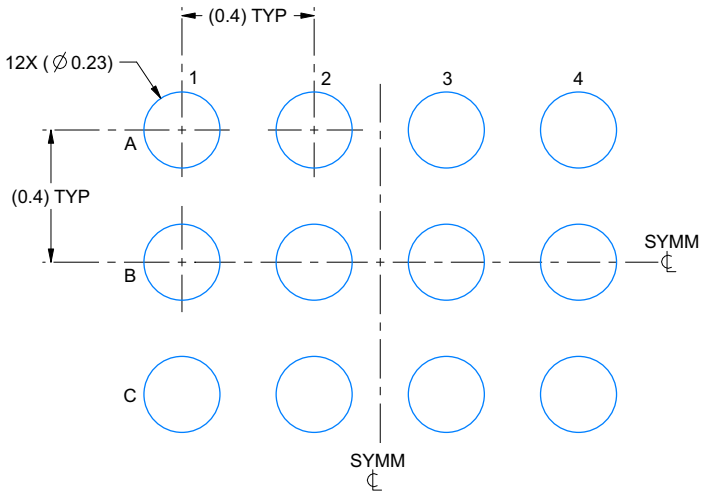
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EXAMPLE BOARD LAYOUT

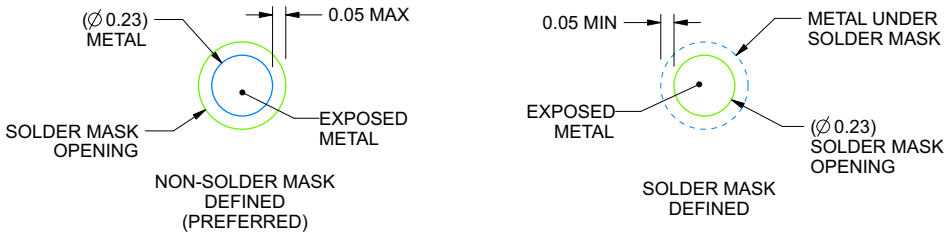
YFP0012-C01

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:50X



SOLDER MASK DETAILS
NOT TO SCALE

4223498/B 04/2017

NOTES: (continued)

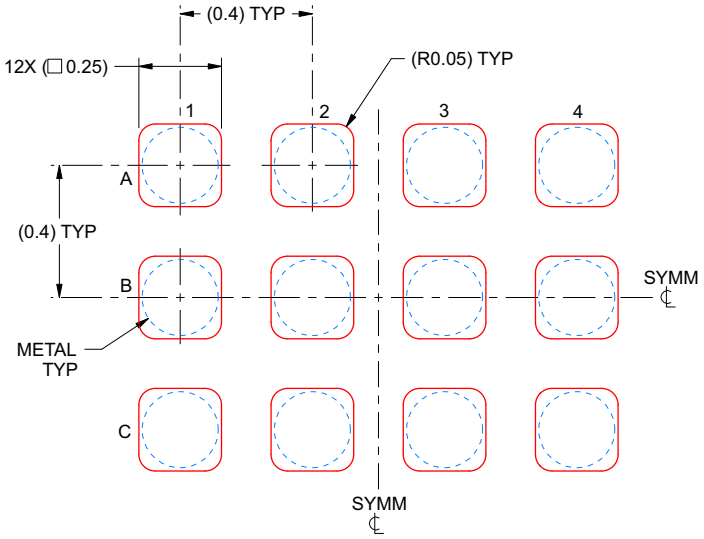
3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).

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EXAMPLE STENCIL DESIGN

YFP0012-C01 — **DSBGA - 0.5 mm max height**

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:50X

4223498/B 04/2017

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TS5USBC400IYFPR	Active	Production	DSBGA (YFP) | 12	3000 | LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	USB4
TS5USBC400IYFPR.A	Active	Production	DSBGA (YFP) | 12	3000 | LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	USB4
TS5USBC400IYFPT	Active	Production	DSBGA (YFP) | 12	250 | SMALL T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	USB4
TS5USBC400IYFPT.A	Active	Production	DSBGA (YFP) | 12	250 | SMALL T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	USB4
TS5USBC400YFPR	Active	Production	DSBGA (YFP) | 12	3000 | LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	0 to 70	USB4
TS5USBC400YFPR.A	Active	Production	DSBGA (YFP) | 12	3000 | LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	0 to 70	USB4
TS5USBC400YFPT	Active	Production	DSBGA (YFP) | 12	250 | SMALL T&R	Yes	SNAGCU	Level-1-260C-UNLIM	0 to 70	USB4
TS5USBC400YFPT.A	Active	Production	DSBGA (YFP) | 12	250 | SMALL T&R	Yes	SNAGCU	Level-1-260C-UNLIM	0 to 70	USB4

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

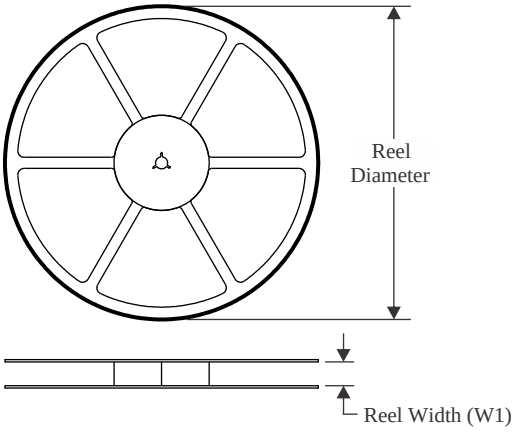
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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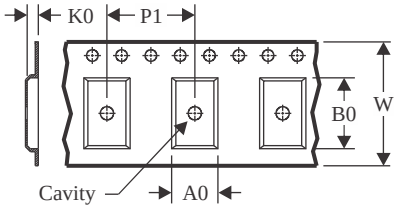
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

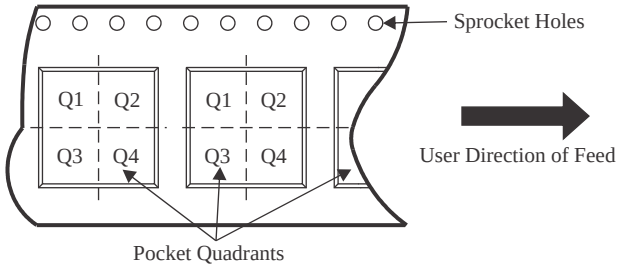


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

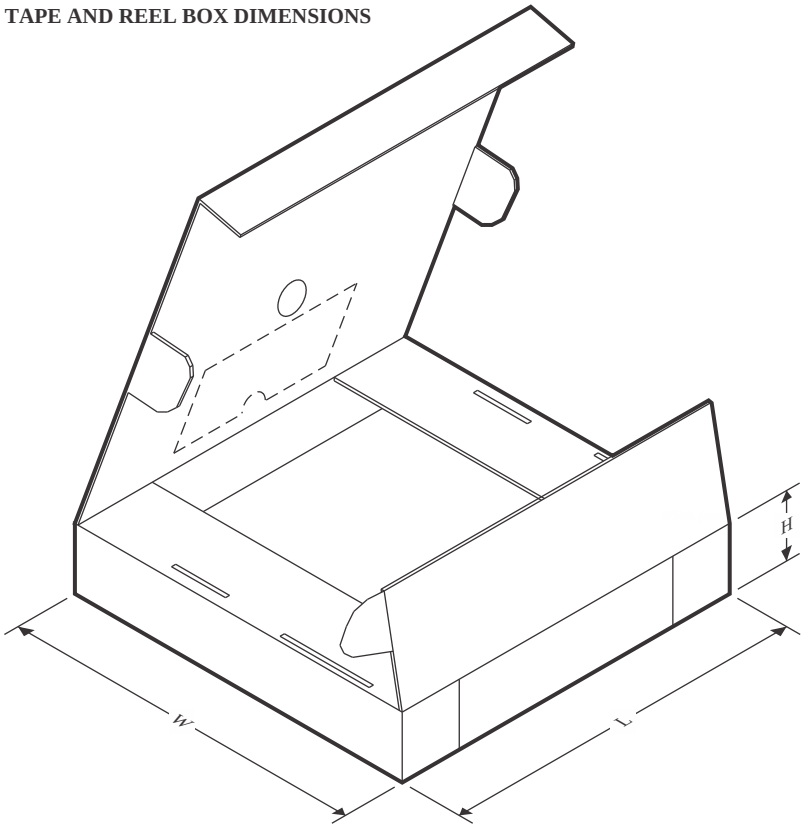
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5USBC400IYFPR	DSBGA	YFP	12	3000	180.0	8.4	1.32	1.72	0.62	4.0	8.0	Q2
TS5USBC400IYFPT	DSBGA	YFP	12	250	180.0	8.4	1.32	1.72	0.62	4.0	8.0	Q2
TS5USBC400YFPR	DSBGA	YFP	12	3000	180.0	8.4	1.32	1.72	0.62	4.0	8.0	Q2
TS5USBC400YFPT	DSBGA	YFP	12	250	180.0	8.4	1.32	1.72	0.62	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5USBC400IYFPR	DSBGA	YFP	12	3000	182.0	182.0	20.0
TS5USBC400IYFPT	DSBGA	YFP	12	250	182.0	182.0	20.0
TS5USBC400YFPR	DSBGA	YFP	12	3000	182.0	182.0	20.0
TS5USBC400YFPT	DSBGA	YFP	12	250	182.0	182.0	20.0

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